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What is claimed is

1. A semiconductor image position sensing device provided with a photoelectric layer generating a photoelectric current in a portion onto which light was input in response to intensity of the light input to the photoelectric layer,

a resistance layer laminated on said photoelectric layer in which the photoelectric current generated in said photoelectric layer flows into a portion corresponding to that onto which said light was input, and

signal current output terminals wherein the photoelectric current generated in said photoelectric layer is distributed in a ratio in response to a resistance value between the signal current output terminals and said resistance layer defined at a position where the photoelectric current was flowed into said resistance layer and from which the photoelectric current is output as an electric current obtained by summing currents over the whole sensing sections altogether, comprising:

a resistance subtracting a photoelectric current having a predetermined distribution of electric current density from photoelectric currents generated in respective portions of the photoelectric layer over the whole sensing sections, and

the photoelectric current subtracted by means of said resistance being adapted to flow into said resistance layer.

2. A semiconductor image position sensitive device as claimed in claim 1, wherein said resistance subtracts an electric current having a predetermined density distribution in a section where each density of the photoelectric currents

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generated in respective sections of said photoelectric layer in response to incident light is higher than the predetermined electric current density, while said resistance subtracts an electric current having a density distribution corresponding to that of the photoelectric current in a section where each density of the photoelectric currents is lower than that of said predetermined electric current density.

3. A semiconductor image position sensitive device as claimed in any one of claims 1 and 2, wherein said photoelectric layer generating a photoelectric current in response to intensity of light is separated into plural portions and they are adapted to act as individual photoelectric devices, respectively, photoelectric currents generated in the photoelectric device which have been separated into the plural portions are adapted to flow concentratively into the resistance layer in each of the portions corresponding to respective positions, an electric current to be subtracted having a predetermined distribution of electric current density is the one obtained by putting them corresponding to the respective separated photoelectric devices together, and remainders as a result of subtraction from the photoelectric currents of the separated photoelectric devices, respectively, are adapted to flow into the resistance layer.

4. A semiconductor image position sensitive as claimed in claim 3, wherein an electric current obtained by subtracting an electric current put together from a photoelectric current is adapted to flow into the resistance layer in the case where photoelectric currents generated in response to projectile

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light in the respective separated photoelectric devices are larger than an electric current obtained by putting together an electric current to be subtracted having a predetermined distribution of electric current density with respect to those corresponding to the respective separated photoelectric devices, while an electric current obtained by subtracting the photoelectric currents generated in the photoelectric devices is adapted to flow into the resistance layer in the case where the former photoelectric currents are smaller than the latter electric currents.